

Advansic Electrostatic Chuck

Features

- Enable to apply for wide range of temperature. (Room temperature to 200 celusius degree)
- Excellent for chucking and de-chucking performance. (Within 2 seconds)
- Excellent surface conditions. ($Ra < 0.01 \mu m$)
- Superior cooling performance. ($30w/mK$)
- Fewer metal impurities and particles on the chucking surface.
- Excellent durability against F and O plasma.
- Long life



| Items | | |
|--|------------------------|--------------------|
| Purity (Except Al Si) | | 4N |
| Contamination on Silicon Wafer | atoms/cm ⁻² | < 10 ¹⁰ |
| Particles on Silicon Wafer | Counts/8inch | <500 |
| Chucking Force (Without dots) | gf/cm ² | >2500 |
| Chucking/Dechucking Time | sec | <2 |
| Seal of Back Side Gas (5kPa) | sccm | <0.5 |
| Thermal Conductivity at R.T. at 200°C | W/mk | 30 22 |
| Flatness of Chucking Surface | μm | 2 |
| Surface Roughness | μm | 0.01 |